

Resonant indirect exchange via remote 2D channel

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We apply the resonant indirect exchange interaction theory to explain the ferromagnetic properties of the hybrid heterostructure consisting of a InGaAs-based quantum well (QW) sandwiched between GaAs barriers with a remote Mn delta-layer. The experimentally obtained dependence of the Curie temperature on the QW depth exhibits a maximum related to the region of resonant indirect exchange. We suggest the theoretical explanation and a fit to this dependence as a result of the two contributions to ferromagnetism - the intralayer contribution and the resonant exchange contribution provided by the QW.

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I. INTRODUCTION

Dilute magnetic semiconductors (DMS) have been attracting a lot of attention for quite a while [1]. A lot of efforts have been put forward to combine the numerous advantages of semiconductors with the spin-related phenomena introduced by the magnetic impurities. In this field, however, still much remains unclear. For instance, the details of the mechanism responsible for the ferromagnetic properties of GaAs doped with a small amount of Mn has not yet been clarified [2]. It is commonly accepted that the ferromagnetism in (Ga,Mn)As is due to the indirect exchange interaction mediated by the holes. The highest Curie temperature achieved for bulk dilute (Ga,Mn)As samples is near 200K which is still far below the room temperature [3]. While it is the Mn solubility limit that basically prevents the increase of T_c in bulk samples [4], the indirect exchange depends on the concentration of the holes. In this regard the GaAs heterostructures with a Mn layer coupled to a remote 2D holes channel have gained a considerable interest [5–8]. It has been demonstrated that GaAs heterostructure with a Mn δ -layer located in a vicinity of $\text{In}_x\text{Ga}_{1-x}\text{As}$ quantum well (QW) shows ferromagnetic behavior similar to that of the bulk Mn-doped GaAs DMS. It was discovered, however, that the dependence of the Curie temperature on the QW depth shows a non-monotonic behavior [9]. It was suggested that the non-monotonic behavior originates from falling of the hole bound state at Mn ion into the energy range of occupied 2D heavy holes subband of the first QW size quantization level [10]. A theory of the indirect exchange via a remote conducting

channel was developed in [10],[11]. The theory predicted enhancement of the exchange interaction strength due to resonant tunnel coupling of a bound state at magnetic ion with the continuum of delocalized 2D states in the channel. In this paper we present a comparison with the experimentally observed dependence of the Curie temperature on the QW depth and analyze how the temperature affects the indirect exchange interaction in the resonant case. As soon as we are talking about 2D structures, the QW and the Mn δ - layer, one should be aware of what is meant by the Curie temperature as there is no possibility of spontaneous breaking of a continuous (rotational) symmetry in our 2D Heisenberg ferromagnet. In our theoretical considerations we actually consider the mean effective exchange constant, i.e. the energy of the indirect exchange interaction between the two neighbouring Mn ions. For a 3D bulk case it is indeed close to the critical Curie temperature for the system to undergo the ferromagnetic phase transition. In the 2D case, however to leave the things consistent it is reasonable to define the Curie temperature as the one marking the onset of 'local ferromagnetic order', when the magnetic correlation length well exceeds the distance between the Mn ions. In the experiment the so defined Curie temperature is obtained from a maximum (bump) on the dependence of in-plane electrical resistance vs temperature which is known to be related to the onset of the ferromagnetic order [12],[13]. For more detailed discussion on the critical temperature in the system under study see Ref.[14],[15].

II. THEORY OF RESONANT INDIRECT EXCHANGE

We consider the problem of resonant indirect exchange between two magnetic ions i and j via a remote 2D chan-

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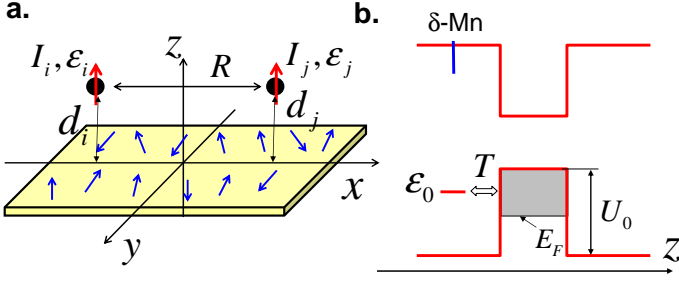


FIG. 1. The illustration of the indirect exchange interaction via remote channel (a) and band diagram of a InGaAs-based heterostructure with a QW and a remote Mn δ -layer (b).

nel as shown schematically in Fig 1a. Here $I_{i,j}$ is the spin projection of the i th(j th) magnetic ion, $\varepsilon_{i,j}$ is the ions' bound state energy, $d_{i,j}$ the distances between the ions and the channel. Indirect exchange interaction mediated by free carriers is usually described on the basis of Ruderman-Kittel-Kasuya-Yosida (RKKY) theory [16]. Separation of the magnetic ions from the free carriers gas by a potential barrier leads to the suppression of the effect due to weak penetration of the 2D carriers wavefunction into the region containing magnetic centers. However, if a magnetic ion possess a bound state having the energy within the 2D gas energy spectra a resonant tunneling may occur. The resonant coupling of a bound state with the 2D continuum prevents the problem to be straightforwardly attacked with RKKY approach. The Hamiltonian of the two magnetic ions i, j coupled to the free electron gas can be expressed in the tunneling Hamiltonian formalism:

$$H = H_0 + H_T + H_J, \quad (1)$$

where H_0 – the Hamiltonian of the system without tunnel coupling and spin-spin interaction, H_T – the tunnelling term, H_J – the exchange interaction term. In the second quantization representation:

$$\begin{aligned} H_0 &= \varepsilon_i a_i^+ a_i + \varepsilon_j a_j^+ a_j + \int \varepsilon_\lambda c_\lambda^+ c_\lambda d\lambda, \\ H_T &= \int (t_{i\lambda} a_i^+ c_\lambda + t_{j\lambda} a_j^+ c_\lambda + h.c.) d\lambda, \\ H_J &= JA (I_i s a_i^+ a_i + I_j s a_j^+ a_j), \end{aligned} \quad (2)$$

where a_i^+, a_i are the creation and annihilation operators for the bound states at the impurity ion i , characterized by the energy level ε_i and localized wavefunction ψ_i , c_λ^+, c_λ are the creation and annihilation operators for a continuum state characterized by the quantum number(s) λ , having the energy ε_λ and the wavefunction φ_λ , J is the exchange constant, A is the squared wavefunction amplitude at the ions site, s is the 2D carrier's spin projection, $t_{i,\lambda}$ is the Bardeen's tunneling matrix element given by [10]:

$$t_i(k) = \sqrt{\frac{\hbar^2 T_i}{2\pi m}} e^{ikR_i}, \quad (3)$$

where m is the 2D continuum density of states effective mass, T_i is the energy parameter for the tunneling:

$$T_i = \alpha U_0 e^{-2qd_i}, \quad (4)$$

where U_0 is the height of the potential barrier separating the magnetic centers from the channel, $q = \sqrt{2m_\perp U_0}/\hbar$, m_\perp being an effective mass in the direction of the tunneling, the dimensionless parameter α depends on the channel and magnetic centers details [11]. We obtained the exchange interaction energy between the two ions in the form [10], [17]:

$$E_{ij} = \frac{1}{\pi} \int_0^{E_F} d\varepsilon \arctan \left[\frac{8\pi^2 j^2 T_i T_j J_0(kR) Y_0(kR)}{((\varepsilon_i - \varepsilon)^2 - j^2)((\varepsilon_j - \varepsilon)^2 - j^2)} \right], \quad (5)$$

where $j = JA|I||s|$ is the exchange interaction strength, E_F denotes the Fermi level of the carriers in the channel (zero temperature is assumed), $k = \sqrt{2m\varepsilon}/\hbar$, J_0, Y_0 are Bessel and Neumann functions of zeroth order,

The formula (5) accounts both for the case of resonant and non-resonant tunnel coupling between the magnetic ions and the channel. The resonant case corresponds to the bound states energy lying within the energy range of the occupied states in the 2D channel:

$$\varepsilon_i, \varepsilon_j \in [0, E_F]. \quad (6)$$

In this regime the main contribution to the exchange energy (5) comes from the poles of the arctangent argument and can be estimated as

$$\begin{aligned} E_{ij} &\approx \gamma \sqrt{jT}, & \text{if } \beta > 1 \\ E_{ij} &\approx \gamma \beta \sqrt{jT}, & \text{if } \beta < 1 \\ \beta &= \frac{\sqrt{jT}}{|\varepsilon_i - \varepsilon_j|}, \quad T = \sqrt{T_i T_j}. \end{aligned} \quad (7)$$

Here γ is given by:

$$\gamma = \sqrt{2\pi} [J_0(k_i R_{ij}) Y_0(k_i R_{ij}) + J_0(k_j R_{ij}) Y_0(k_j R_{ij})]^{1/4}, \quad (8)$$

where R_{ij} is the distance between the ions. γ is the parameter that incorporates the oscillating behavior of the indirect exchange in the similar way that standard RKKY theory does. Unlike RKKY theory, here the Fermi wavevector k_F is replaced by the 'resonant' wavevectors corresponding to the bound levels: $k_i = \sqrt{2m\varepsilon_i}/\hbar$. For the experimental situation considered below the parameter γ appears to be $\gamma \approx 1$ being still far from the first maximum of the oscillations. The approximation (7) is quite good as illustrated in Fig. 2. The dotted curve shows the exchange interaction energy calculated according to (5) for the case $\varepsilon_i = \varepsilon_j = \varepsilon_0$, while the solid curve shows the approximation (7) assuming $\gamma = 1$. The value of the exchange energy in the resonant case is much larger than in the non-resonant one. The latter case agrees well with the RKKY approach, the integration (5) for the case when the arctangent argument

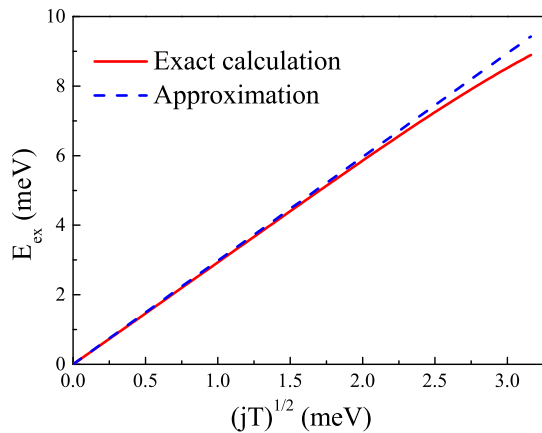


FIG. 2. Approximation for indirect resonant exchange energy (dashed line) compared to exact result (solid line).

has no poles and therefore is small as far as the tunneling is weak yields [10]:

$$E_{nr} = \frac{8\pi T^2 j^2 E_F}{\varepsilon_0^4} \chi(R),$$

$$\chi(R) = J_0(k_F R) Y_0(k_F R) + J_1(k_F R) Y_1(k_F R), \quad (9)$$

where R denotes the mean distance between the ions. Note that the resonant and non-resonant cases have different parametric dependence on the tunneling parameter T and the exchange parameter j , this leads to substantial amplification of the indirect exchange in the resonant case.

III. COMPARISON WITH EXPERIMENT

We applied the theory of the resonant exchange to the hybrid InGaAs-based semiconductor heterostructure doped with a δ -layer of Mn, which have been also studied experimentally. The energy diagram for the system under study is shown schematically in Fig.1b. It is a GaAs/Mn δ -layer/GaAs/In $_x$ Ga $_{1-x}$ As/GaAs heterostructure. The Mn content (Mn layer effective thickness) is 0.25-0.3 monolayers (ML), the spacer thickness d , between the Mn layer and the In $_x$ Ga $_{1-x}$ As quantum well (QW) is $d = 3$ nm, the thickness of the QW is 10 nm and its depth is controlled by In concentration x . For detailed description of the structure see [8]. The samples were shown to exhibit ferromagnetic properties, which were found to be non-monotonously dependent on the QW depth [9]. The Curie temperature derived from the resistance anomaly appears to depend on the parameters of the QW thus favouring the idea that the indirect exchange interaction is partly due to 2D holes sitting in the QW. The interaction between the Mn ions mediated by the 2D holes in the QW must be considered with account for the resonant indirect exchange, because the acceptor binding energy of Mn in GaAs is comparable to the QW depth

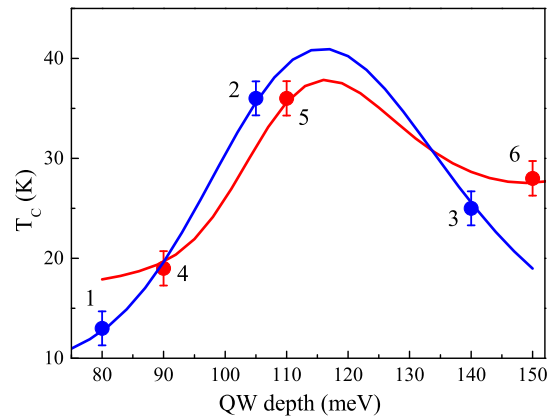


FIG. 3. Dependence of the Curie temperature on the QW depth. Experimental data (circles) and the theoretical fit (solid curves).

for the holes. This makes it possible to meet the resonant condition (6). This very case is shown in Fig. 1b, where ε_0 denotes the average energy of the bound state of a hole at Mn in the δ -layer (zero energy corresponds to the first heavy holes quantization level in the QW). It is also worth noting that in real samples the Mn δ -layer has a certain width. In fact due to the Mn ions diffusion its halfwidth is known to be around 1.5 nm [18]. It is thus natural to expect that the exchange via QW is not the only contribution, i.e. without QW the ferromagnetic properties of the Mn layer would be resembling the bulk ferromagnetism of a dilute magnetic semiconductor sample of a small yet finite thickness around 3 nm. The ferromagnetic properties of the Mn δ layer embedded into GaAs matrix has been also studied theoretically [19]. We made a fit to the experimental data [9] (circles in Fig.3) assuming that there are two contributions to the indirect exchange interaction between the Mn ions. The first one is assumed to be itinerant ferromagnetism of the Mn δ -layer itself due to the weakly localized holes located primarily in this layer in the same manner as the ferromagnetism in the bulk dilute GaMnAs semiconductor is believed to emerge. This contribution does not depend on the QW properties. The second contribution is the resonant indirect exchange via the 2D holes of the QW. This one is treated on the basis of our theoretical result (5). We demonstrate that the maximum of the Curie temperature corresponds to the resonant indirect exchange via the 2D holes of the QW while its decrease for both too shallow or too deep QW is explained by driving the system out of the resonance (6). In our calculation we assumed the Curie temperature being the sum of the two terms:

$$T_C = T_{C1} + T_{C2}, \quad (10)$$

where T_{C1} does not depend on the QW properties. In calculation of the second term T_{C2} we assumed that the energy levels at Mn ions are normally distributed having an average value ε_0 and dispersion σ_ε . The distance be-

tween the neighbouring ions was assumed to be constant, equal to the mean one R . For the Mn δ -doping of 0.3 ML one can take $R = 1.5$ nm. We checked that taking into account some distribution over the distances as well as varying the mean value has little effect on the resonant exchange term. This is because γ defined by (8) is a very weak function of R in the vicinity of $\gamma = 1$. On the contrary, the Mn bound levels energy distribution does play an important role and must be accounted for. In order to introduce the energy levels distribution into the fitting procedure it is convenient to replace the approximation (7) by a similar function:

$$\tilde{E}(\varepsilon_i, \varepsilon_j) = \frac{\gamma^2 jT}{|\varepsilon_i - \varepsilon_j| + \gamma\sqrt{jT}} \quad (11)$$

The resonant contribution to the Curie temperature T_{C2} (10) is calculated using the following expression:

$$T_{C2} = \frac{2}{k_B} \int_0^{E_F} d\varepsilon \int_{-\infty}^{+\infty} d\varepsilon' P(\varepsilon)P(\varepsilon')\tilde{E}(\varepsilon, \varepsilon'), \quad (12)$$

where:

$$P(\varepsilon) = \frac{1}{\sqrt{2\pi}\sigma_\varepsilon} e^{-\frac{(\varepsilon-\varepsilon_0)^2}{2\sigma_\varepsilon^2}}, \quad (13)$$

k_B is the Boltzmann constant. In the limiting case of a delta-like bound states energy distribution $\sigma_\varepsilon \rightarrow 0$ the expression (12) yields:

$$T_{C2} = \begin{cases} \frac{2}{k_B}\gamma\sqrt{jT}, & \varepsilon_0 \in [0, E_F] \\ 0, & \text{otherwise} \end{cases}, \quad (14)$$

i.e. the resonant contribution vanishes whenever ε_0 goes below or above the energy range occupied by the carriers in the QW. The approach was used to fit the experimental values of the Curie temperature measured for two series of samples. The samples 1-3 had 0.25 ML of Mn and the QW depth for the holes U_0 varied from 80 to 140 meV, the samples 4-6 had 0.3 ML of Mn with U_0 varied from 90 to 150 meV. The two theoretical fits for the two series of experimental points are presented in Fig.3. The average value of the Mn bound state for the best fit was $\varepsilon_0 = U_0 - 103$ meV, i.e. 103 meV above the top of the valence band for GaAs, which roughly matches the Mn acceptor binding energy (≈ 110 meV). This value was the same for the two fits. The holes concentration and thus the holes Fermi level was derived independently from the transport experiments [8],[20] and the QW depth from the optical experiments. These values are given in the Table 1 along with the other parameters of the fit. Along with the mean bound state energy the fitting parameters were the non-resonant component of the Curie temperature T_{C1} , the bound state energy dispersion σ_ε and the product jT , assumed to be the same for all the ions in the layer. As it is seen from Table 1, for the fit covering samples 4-6 T_{C1} appeared to be higher than for the samples 1-3, this is consistent with the latter having weaker

No	T_c , K	U_0 , meV	p , cm^{-2}	E_F , meV	T_{C1} , K	\sqrt{jT} , meV	σ_ε , meV
1	13	80	$5.6 \cdot 10^{11}$	7.8	9	3.3	18
2	36	105	$8.9 \cdot 10^{11}$	12.5	9	3.3	18
3	25	140	$1.8 \cdot 10^{12}$	25.2	9	3.3	18
4	19	90	$0.7 \cdot 10^{11}$	1.0	17	4.1	13
5	36	110	$3.0 \cdot 10^{11}$	4.2	17	4.1	13
6	28	150	$2.3 \cdot 10^{12}$	32.2	17	4.1	13

TABLE I. The parameters of the fit

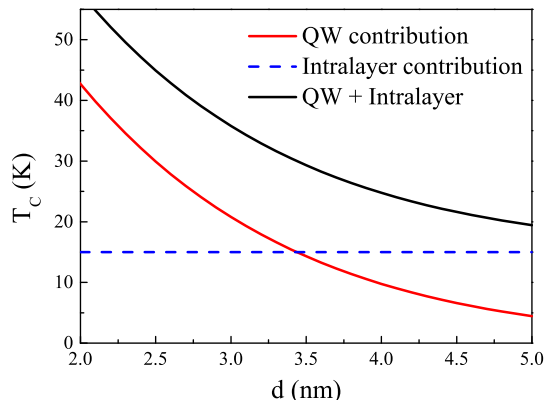


FIG. 4. The calculated dependence of the Curie temperature on the distance between QW and Mn δ -layer.

Mn doping. The larger jT product for the more heavily doped samples can be understood if we recall that the so-called δ - layer of Mn in reality has rather thick spatial distribution, expected to be thicker for larger Mn concentration due to Mn diffusion [8]. Thus, the minimum distance between the Mn layer and the QW is expected to decrease with increase of Mn doping level resulting in increase of the tunneling parameter. The difference in the energy levels dispersion σ_ε perhaps cannot be unambiguously explained with the similar plain arguments. What is read from the fit (Table 1) is that the diagonal disorder is somewhat smaller in the Mn layer with higher Mn concentration. To summarize we conclude that the fit demonstrates good agreement with the experimental data and the obtained values of the fitting parameters seem quite reasonable. Thus, the experimental data can be described by the two contributions as explained above.

It might be also useful to illustrate the interplay between the two contributions to the ferromagnetism. Shown in Fig. 4 is the dependence of the two contributions as a functions of the distance d between the Mn δ - layer and the QW. T_{C1} term is referred as intralayer contribution in Fig. 4. It is, of course, independent of d . The QW contribution does depend on d through the tunneling parameter. For the tunneling case this dependence appears to be weaker than for the non-resonant one as T_C roughly follows the \sqrt{T} dependence (7) rather than T^2 (9). The illustration presented in Fig. 4 corresponds to the parameters of the sample 5 (Table 1) and extrap-

olated to spacer thickness other than that of sample 5 ($d = 3$ nm). We note here that the dependence of T_C on d appears to be still too strong compared to the experimental observations [9]. We attribute this disagreement to the uncertainty in determination of the distance d between Mn layer and QW due to the finite thickness of the Mn layer being around 3 nm. The detailed analysis here requires more experimental data.

IV. SUMMARY

On the basis of the the previously developed theory of the resonant indirect exchange interaction we analyzed the ferromagnetic properties of the hybrid heterostructure consisting of a InGaAs QW and remote Mn layer. The experimentally observed non-monotonous dependence of the Curie temperature on the QW depth was explained and fit as the result of two contributions to ferromagnetism. The first one is the intralayer con-

tribution stems from the same mechanism as that of the ferromagnetism in bulk dilute GaMnAs samples. The second contribution is the resonant indirect exchange via the 2D holes populating the QW. It is this mechanism that is responsible for the non-monotonous behavior of T_C . As only the second contribution depends on the distance between the QW and Mn layer, further experimental investigations are required to separate the two mechanisms.

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